

**DYNAMIC MEMORY CELL AND METHOD OF MANUFACTURING SAME****ABSTRACT**

5 A memory device has a plurality of memory cells, wherein  
each memory cell has a trench capacitor formed in a  
semiconductor substrate and an access transistor for it.  
Each access transistor has a first contact region connected  
to an internal electrode of the trench capacitor, a second  
10 contact region to a bit line and a control electrode  
region, wherein the control electrode regions of  
neighboring access transistors are connected by a word line  
formed in the semiconductor substrate.